

**9th “Trento” Workshop
on Advanced Silicon Radiation Detectors
Genova, 26-28 February 2014**



Highlights from IBL 3D Module Production

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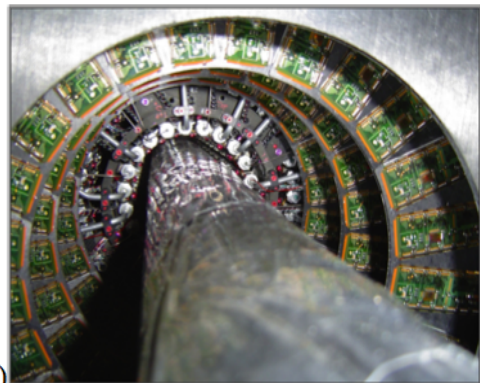
Università degli Studi Di Genova - INFN



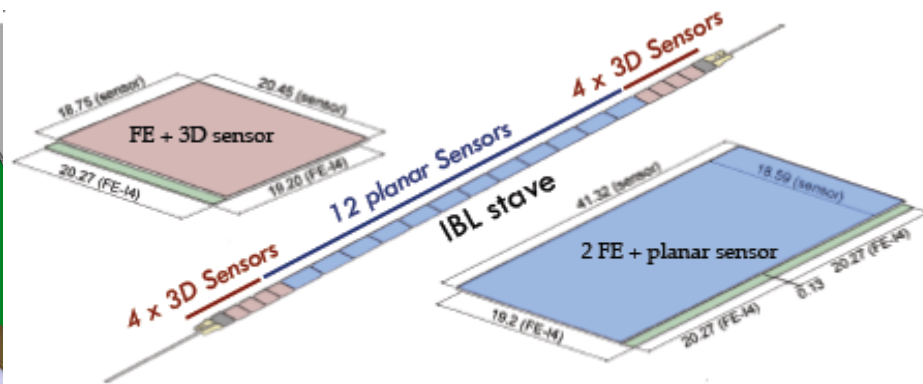
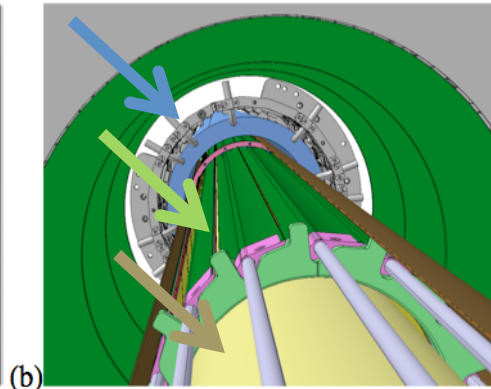


IBL & Staves Overview

Actual Detector



IBL & pixel



The Insertable B-Layer (IBL) is the first upgrade of the ATLAS Pixel detector and it is going to be installed in LS1.

IBL is composed by 14 Staves and each is equipped with:

- ✓ Central region: **12** Double-chip modules (Planar/CiS)
- ✓ Forwarded regions: **4+4** Single-chip modules (**3D FBK & CNM**)

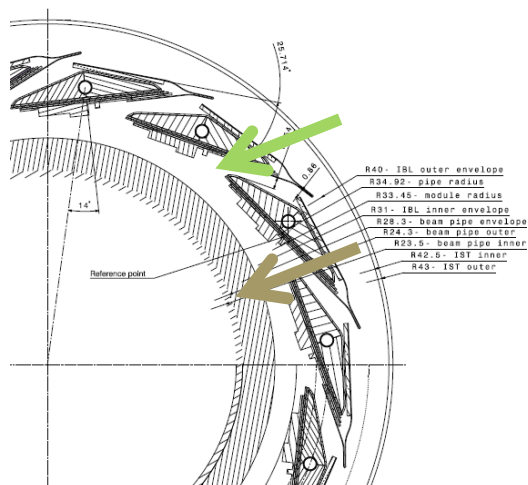
A total of **112** 3D Modules are in the IBL

12 MILLIONS of channels

➤ A new Front End electronics has been developed (**FE-14**)

[see Didier's Talk for more details](#)

- ➡ Actual Pixel Detector
- ➡ IBL
- ➡ New Beam Pipe





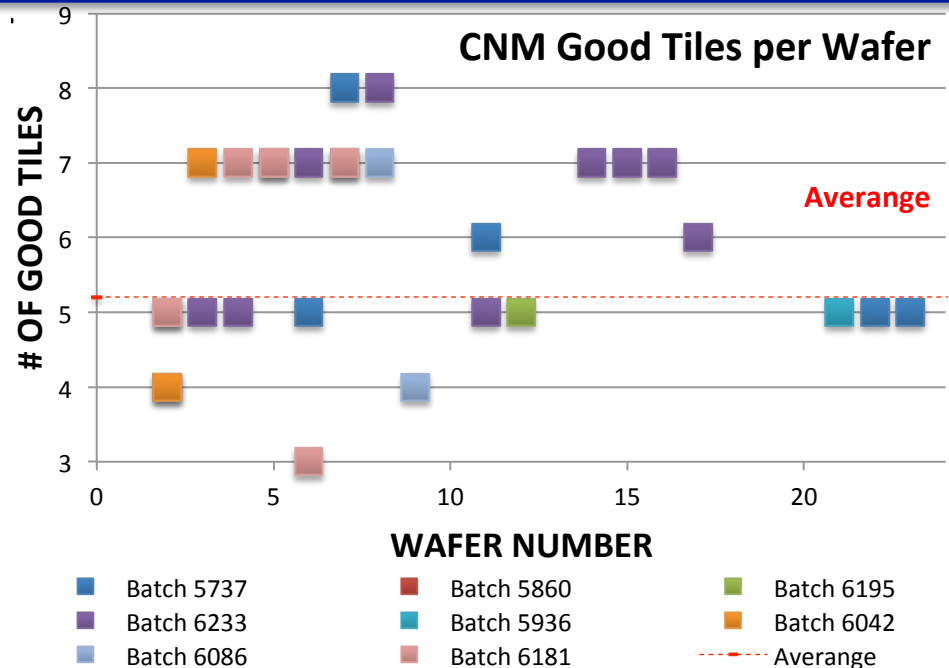
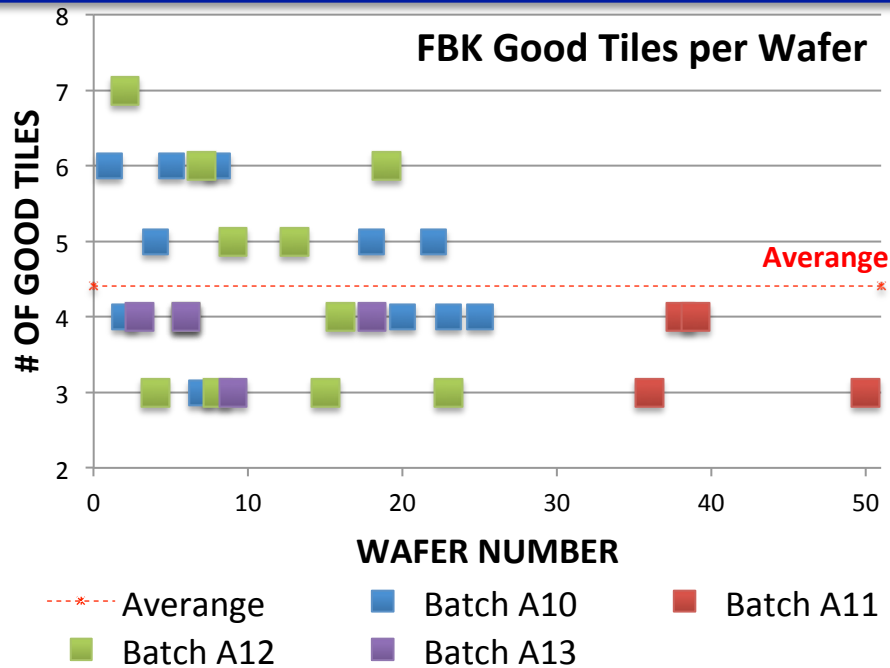
Summary of Production 3D



	Wafer Produced & Tested	Selected Wafer
CNM	50	41
FBK	70	33

	Selected Good Tiles	Delivered Modules to Labs
CNM	228	167
FBK	134	124

V_{bd} IBL Requirement to select tiles is 25 V → A wafer is selected if it has at least 3 good tiles. CNM yield is higher than FBK but FBK measurement on full device, CNM on Guard ring only.





Assembly and Qualification of Modules

BARE

- Check mechanical integrity and sensor IV.

ASSY

- Electrical test at ambient temperature, in which is checked the proper basic functioning of the module (e.g. IV Curve, bumps connectivity). Also done the Tuning at working point of 3ke Threshold and 9BC @ 20ke

BURN

- Module is thermal cycling (-40, +40 °C for 2-3 days) and retested at ambient temperature.

FLEX

- Complete calibration of the module.
- A functionality test with ^{241}Am is done
- All tests are executed at -10 °C.

10 min

60 min

48-72 hours

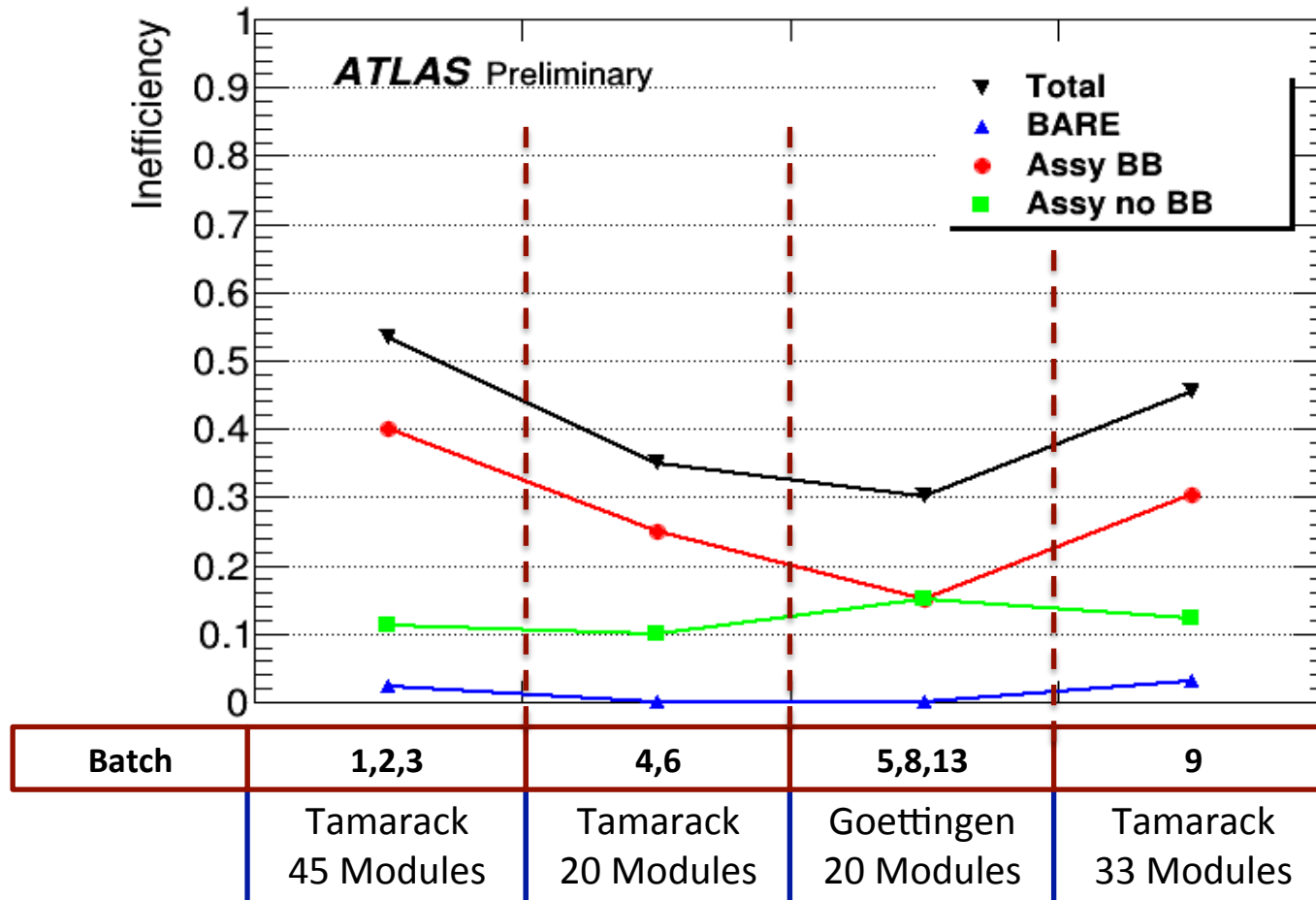
180 min



Yield of 3D Production

FBKs have a bump bonding failure of ~20% (Vs 10 % of CNMs) but a electrical failure rate (including electronics and IV) of only 10%.

FBK YIELD (from 4 onwards): 62%



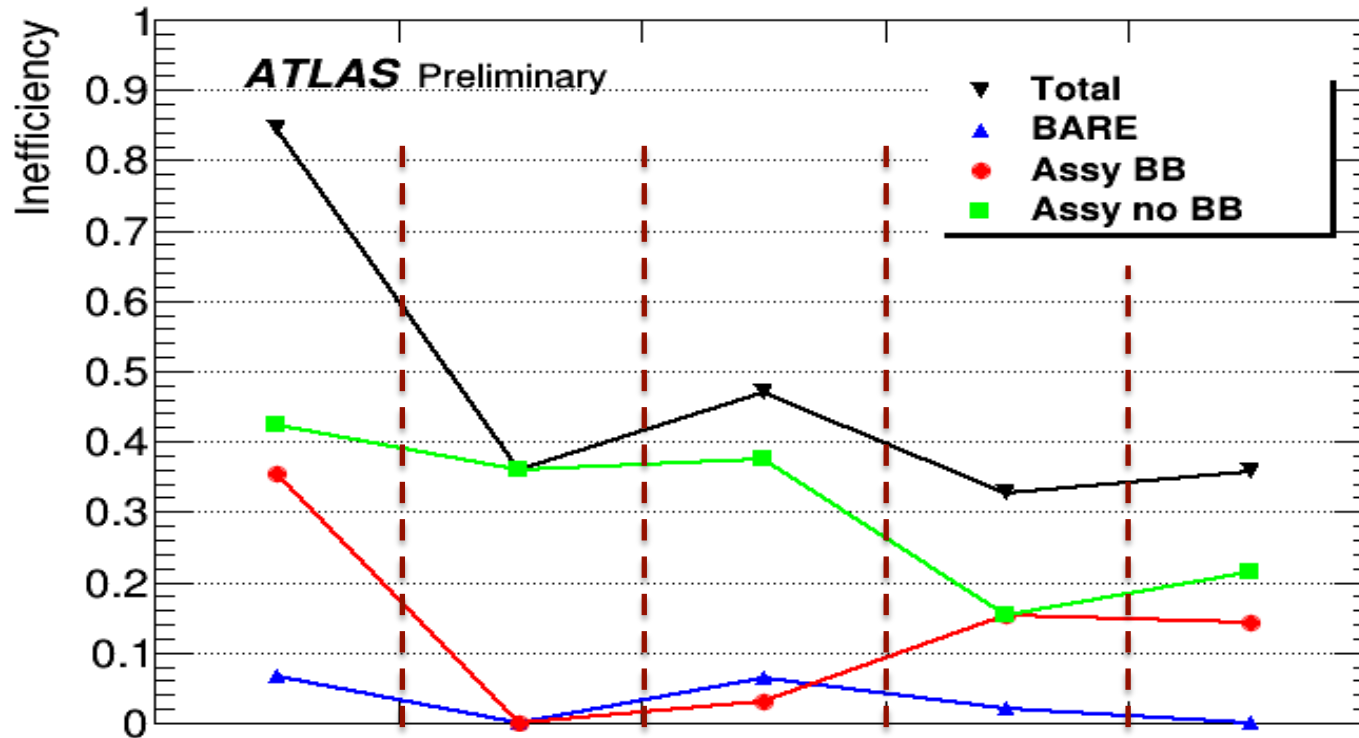
Plot by C. Gemme



Yield of 3D Production

CNMs bump bonding failure rate is better than FBKs (10 % Vs 20%) but they have more electrical failure (mainly IV failure).

CNM YIELD (from 4 onwards): 62%



Batch	1,2,3	4,6,7	5,6	9,10,12	11,13
	Tamarack 45 Modules	Tamarack 25 Modules	Goettingen 32 Modules	Tamarack 52 Modules	Goettingen 14 Modules

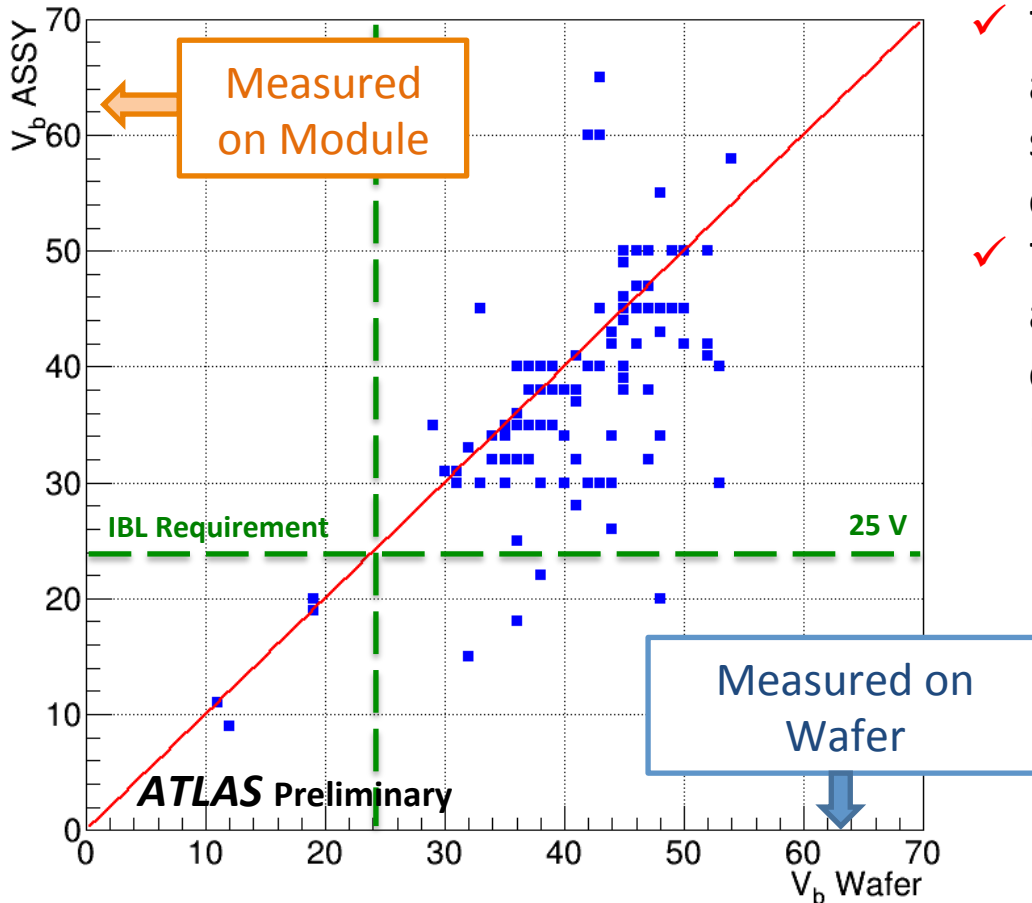
Plot by C. Gemme



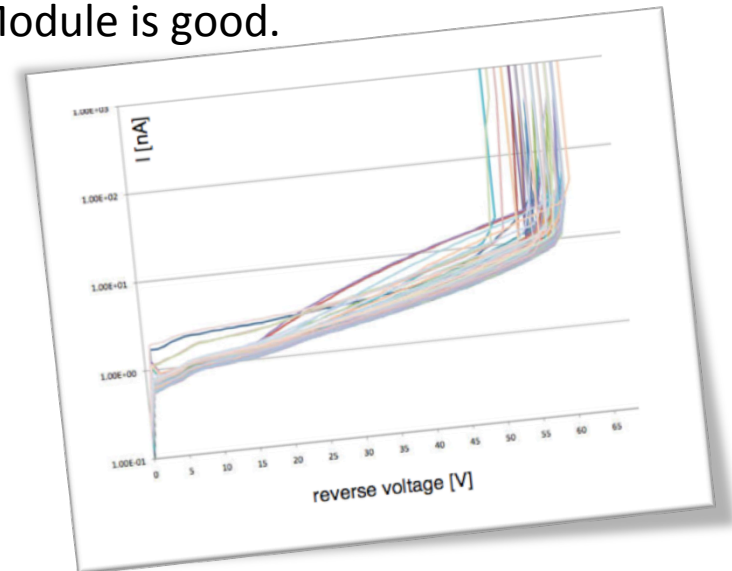
Sensors V Breakdown Changes after the Assembly (FBK Modules)

See Ivan L.'s Talk for CNM

V_b Correlation Wafer/ASSY - FBK



- ✓ FBK deposits a temporary metal layer which allows I-V tests to be performed in each tile.
- ✓ The measurement is performed automatically on the 80 columns of sensors by using a dedicated probe card.
- ✓ Thanks this method is possible to select accurately good tiles and the correlation of V_b between Wafer and Module is good.





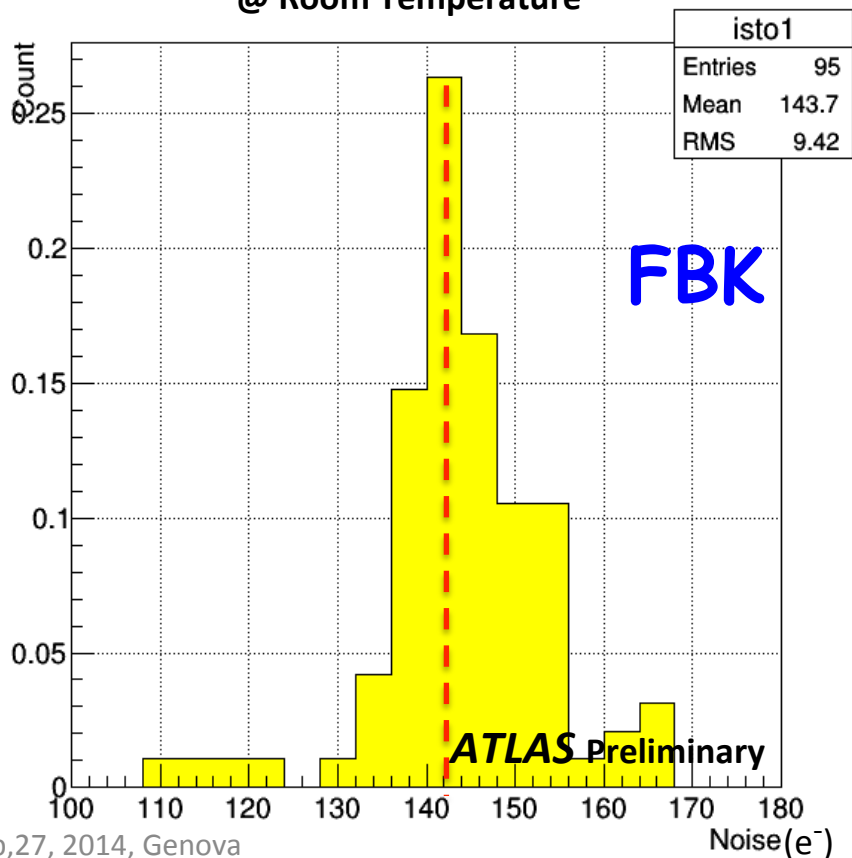
Noise Comparison

The **noise** depends on V_{bias} , temperature and sensor type.

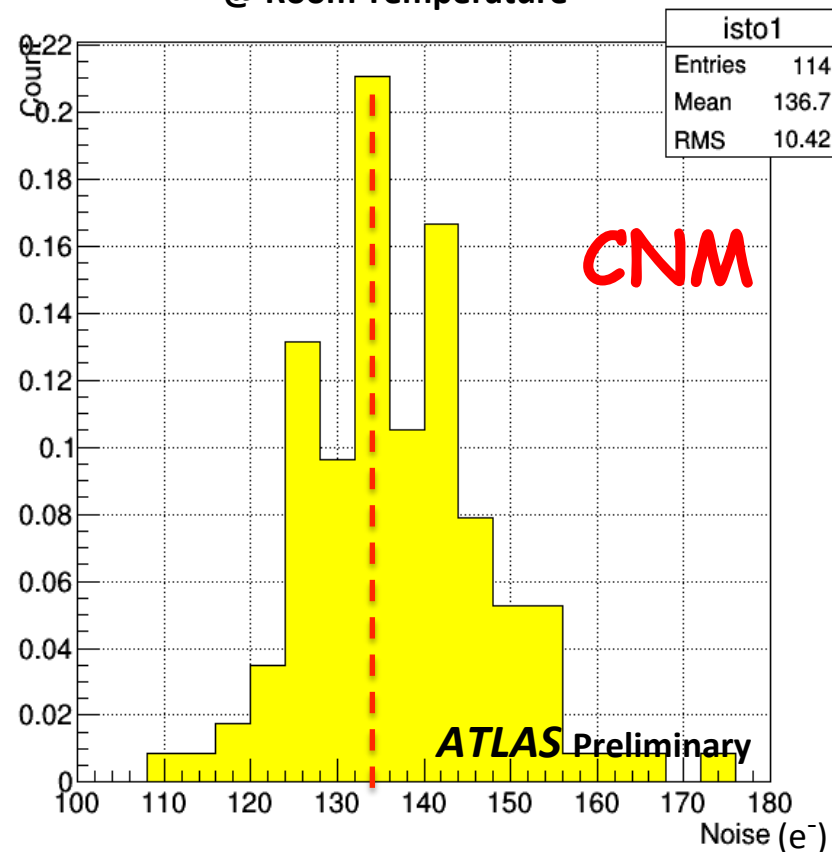
At room temperature and $V_{bias} = 20$ V average values are $\sim 144e^-$ for FBK and $\sim 137e^-$ for CNM (140 e^- and 130 e^- at -10°C).

Here is reported the Noise distribution of all CNM and FBK modules produced (in which the statistic was available)

**FBK NOISE distribution
@ Room Temperature**



**CNM NOISE distribution
@ Room Temperature**

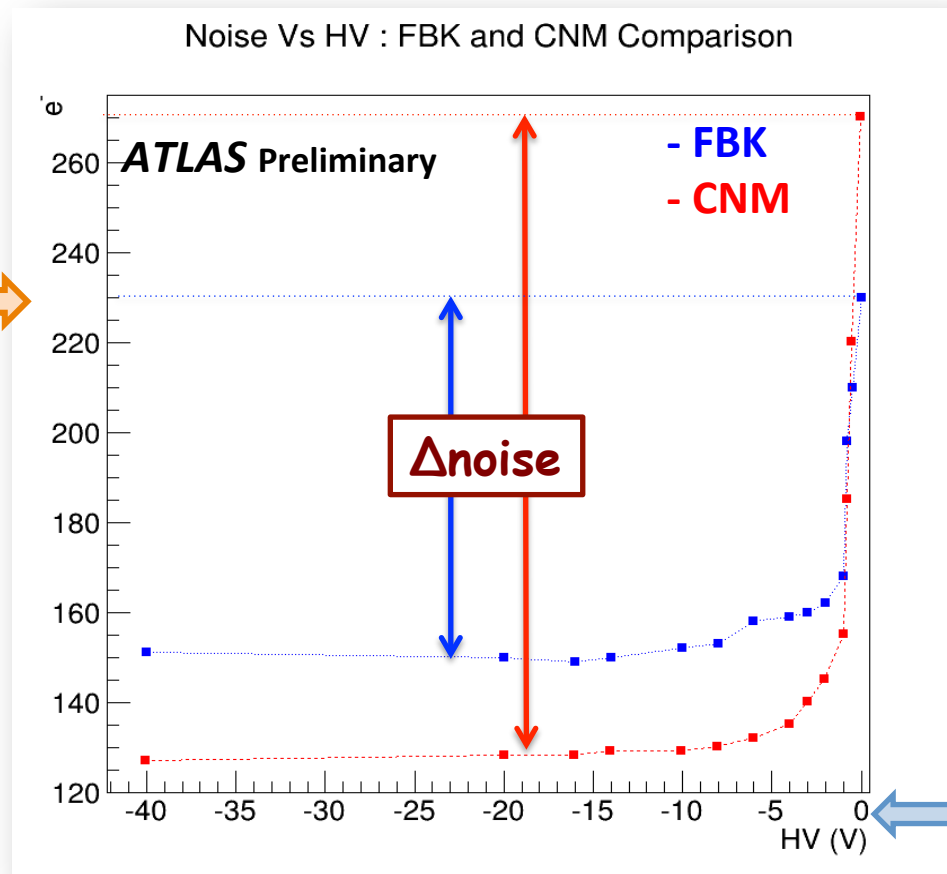




Noise VS High Voltage

Comparison between an **FBK** and a **CNM** device at room temperature for different values of V_{bias} .

The difference of noise between V_{bias} On and Off of FBK is less than CNM.



Δnoise is defined as $\text{Noise}_{\text{HVoff}} - \text{Noise}_{\text{HVon}}$

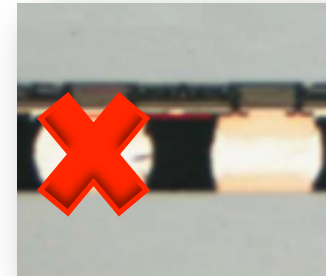
At low temperature the Δnoise is reduced of a \sim factor 2.

Noise

High Voltage

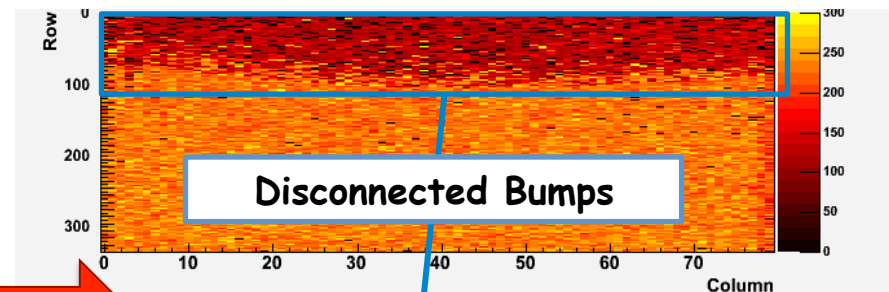
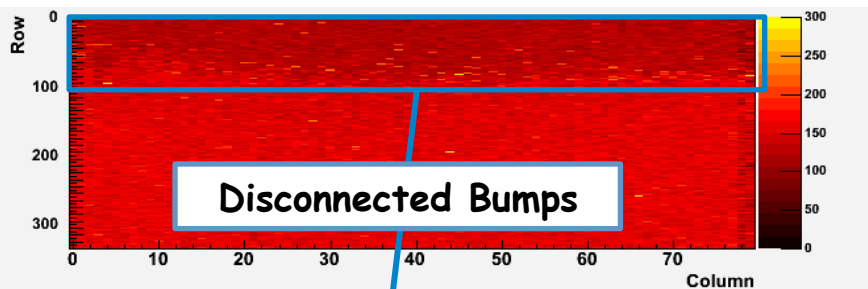


Noise VS High Voltage

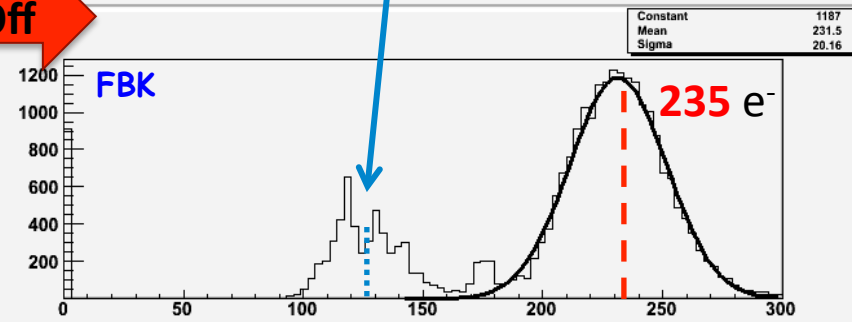
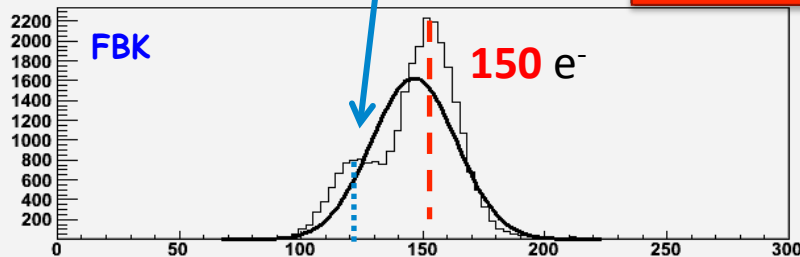


- ✓ For **unconnected bumps** the noise is less than the normal and remains **the same** if the V_{bias} of the sensor is turned off while for connected bumps becomes much higher.
- ✓ From the difference between the distributions of noise with and without HV ($\Delta noise$) and placing an appropriate cut on $\Delta noise$ is possible to estimate the number of unconnected bumps.

➤ A cut of $\Delta noise = 20 e^-$ is very efficient.



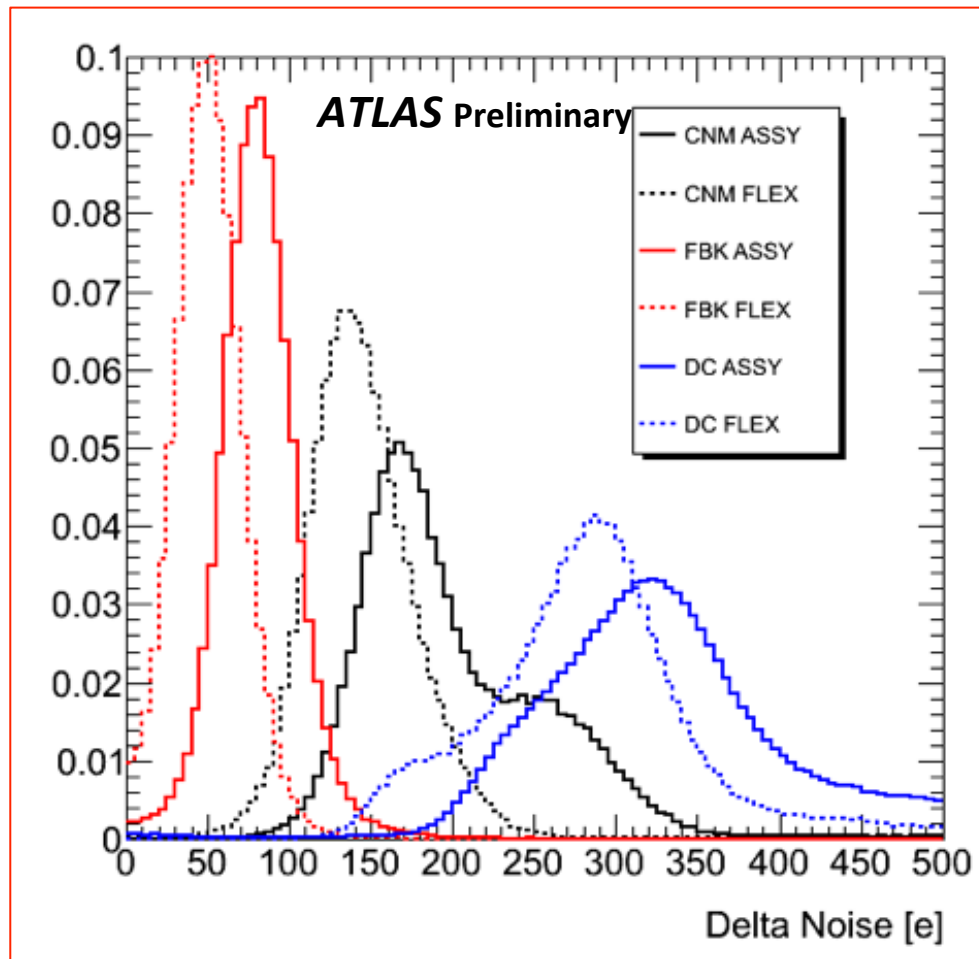
Noise with HV Off





Noise VS High Voltage

The described method at low temperature detects ~10% of faked for FBK.
For this reason also a source scan is used during the the qualification.

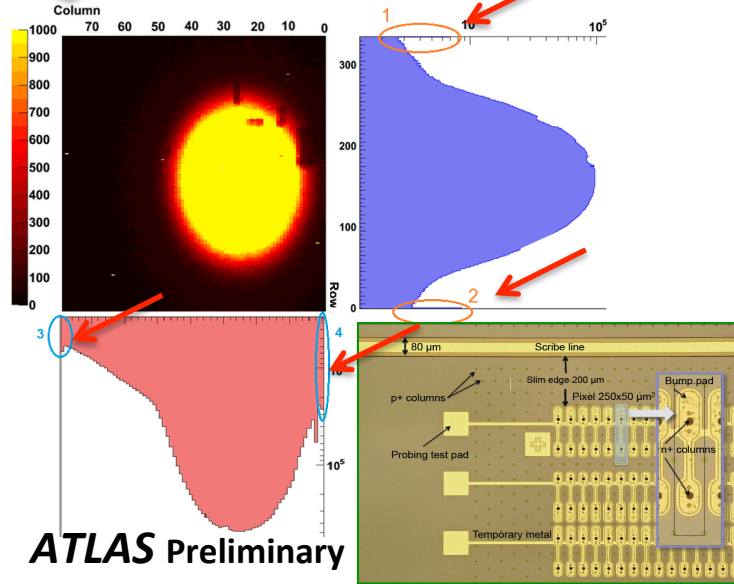


Plot by K.Motohashi



Charge collection at sensor edge

FBK

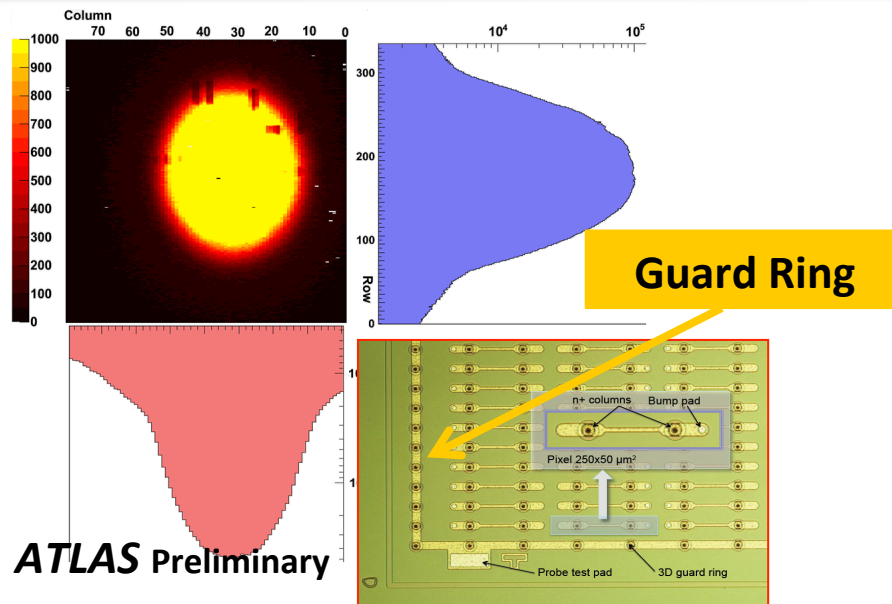


...See Test Beam results in Joern L.'s Talk

The **FBK** edges are partially active: hit occupancy of edge pixels is larger than for the internal pixels.

Source Used: ^{241}Am

CNM



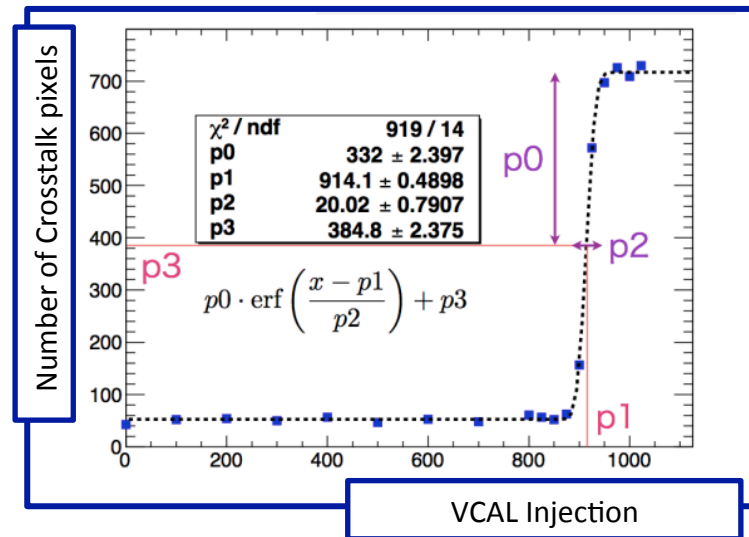
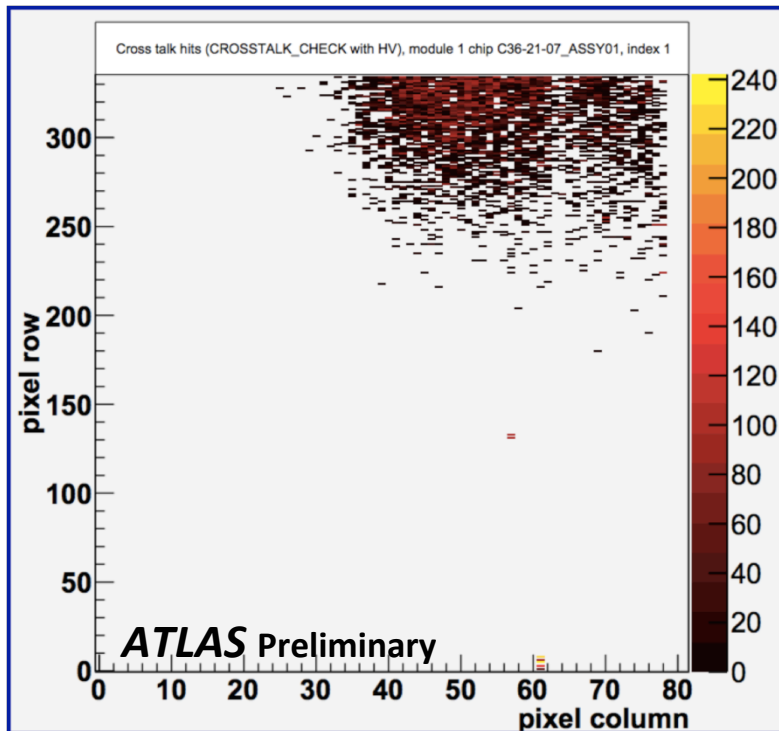
For **CNM** sensors, the guard ring collects the charge outside the pixels area: the hit occupancy of peripheral pixels is therefore the same as the internal ones



Cross-Talk in CNM Devices

The **Cross-Talk** test consists in injecting the maximum charge (the default is a DAC VCal of 1023 equivalent to 55ke⁻ charge) in two neighbouring pixels and measure if any hit is observed. The test is run routinely at 3 ke⁻ threshold and usually the cross-talk is lower than ~3%.

✓ In some CNM devices High Xtalk has been observed (never in FBK).
 ↘ This is not worrisome for the data-taking performance.



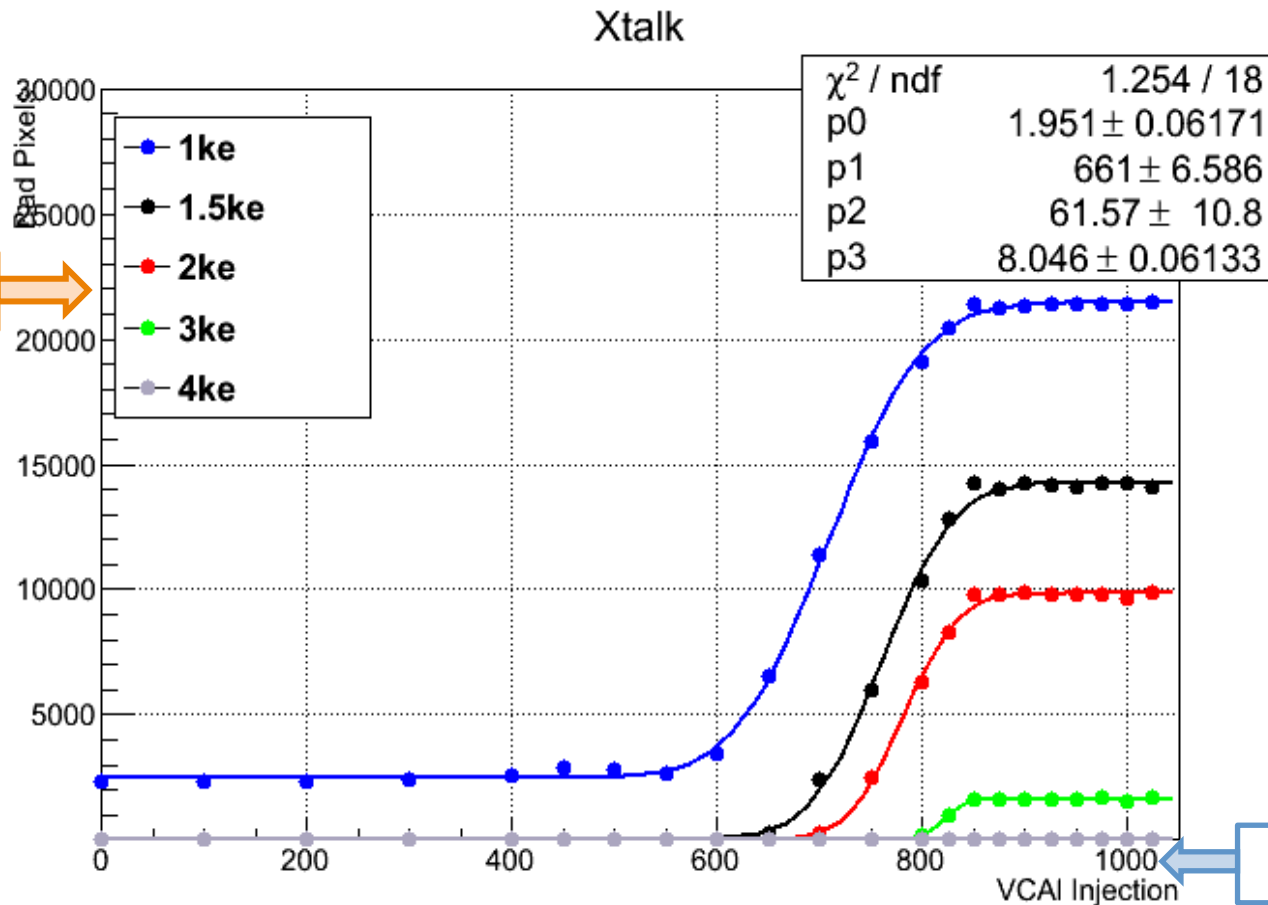
CNM Modules with High Xtalk (on the total CNM mounted)	~5%
CNM Modules with High Xtalk in Good Modules (IBL Quality)	~9%

Plot by K.Motohashi



Cross-Talk Vs Threshold

Crosstalk Pixels Vs charge injected for different values of Threshold.
The Cross-Talk drops at the increase of threshold

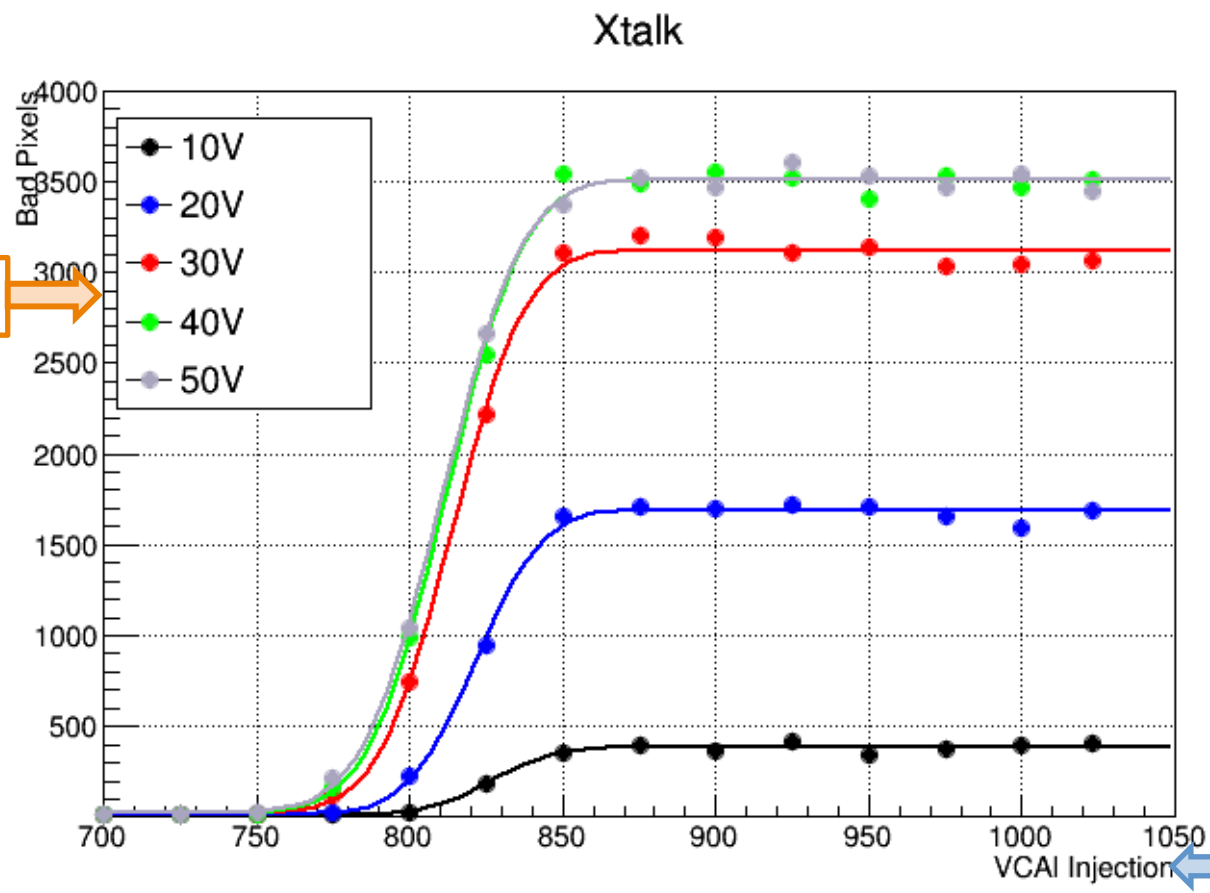


Plot by C. Gemme



Cross-Talk Vs HV

Crosstalk Pixels Vs charge injected for different values of V_{bias} .
The Cross-Talk increases with V_{bias} up to saturation.



Bad Pixels

VCAL Injection

Plot by C. Gemme



Conclusions

- ✓ **The IBL is the first “large scale” 3D detector.**
 - ✓ **3D module production has been a positive experience.**
 - **The large statistic production has spotted some minor but interesting effects that could be important to future developments.**
- A better QA at wafer level is certainly welcome to improve yield and reduce costs.**

Thank you!

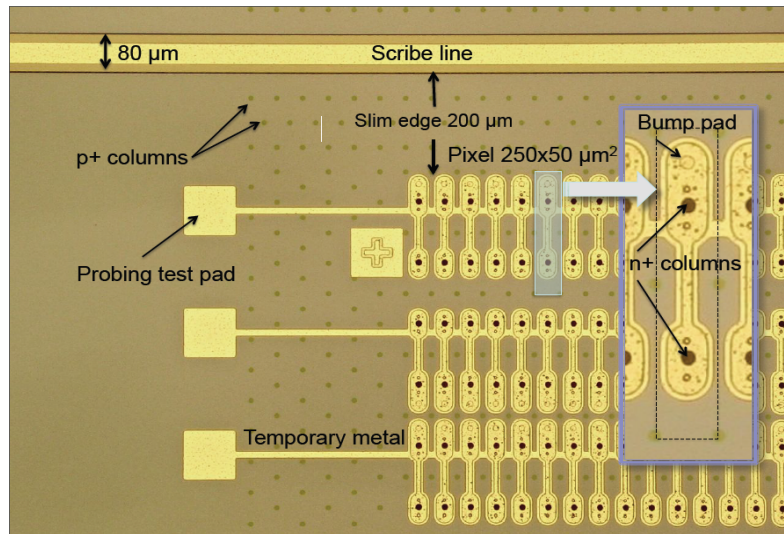


SPARE



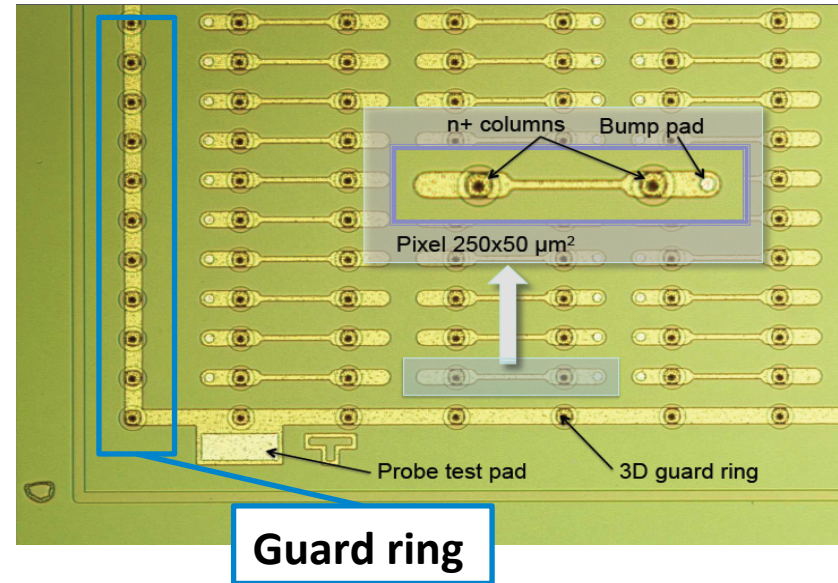
FBK CNM Sensors

FBK



During the leak measure
all pixels are connected

CNM



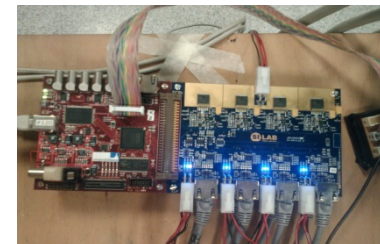
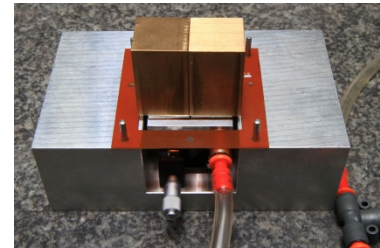
CNM: The leak current is
measured only on the
guard ring



Building and Qualification of Modules

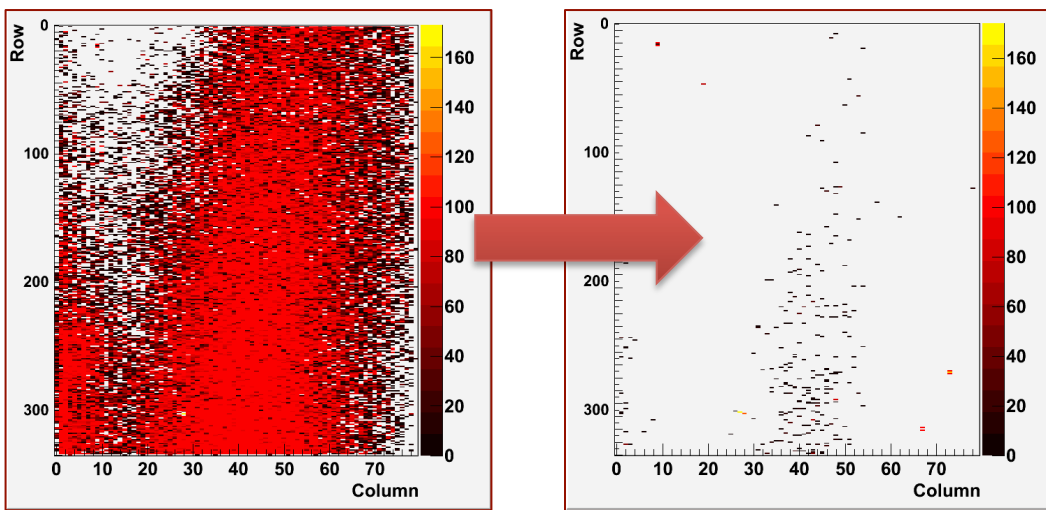
Sensors are flip-chipped at IZM and then delivered to Genova and Bonn for module assembly and testing.

- ✓ Assembly of a module starts with gluing a module pigtail on bare module (SC/DC).
- ✓ Wirebondings are done to the FE pads, to the HV and to the test pads. It is also done a pull test to qualify the quality.
- ✓ Module is tested with USBPix readout system



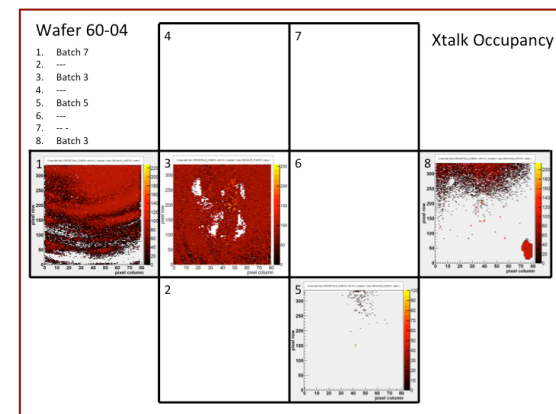
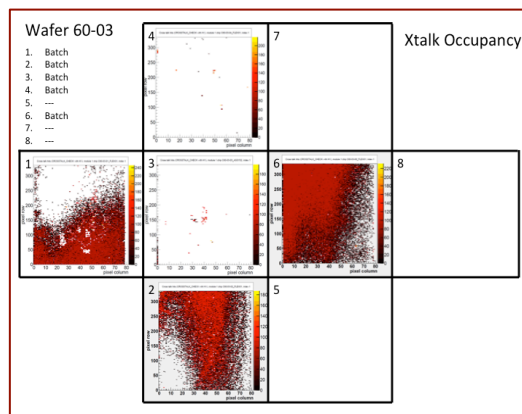


Cross-Talk



- ✓ To observe that changing the injected charge ($V_{cal} = 800$) the Xtalk disappear.
- ✓ For this reason has been implemented during the production Xtalk scans with both charge injection (1023 and 800)

It is also interesting to observe that a good part of CNM modules with high Crosstalk seems to derive from the same wafers.



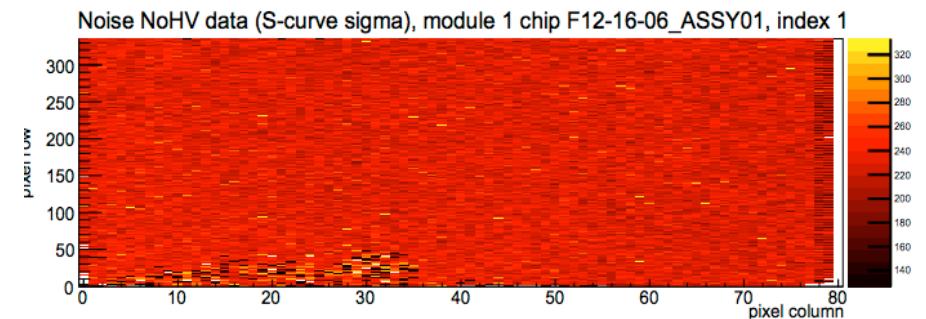
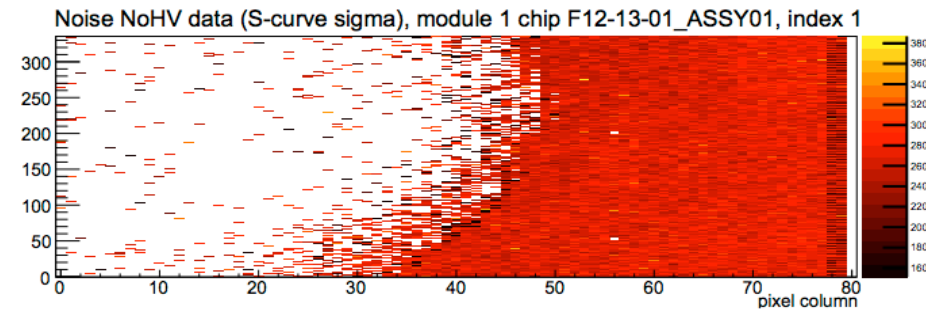
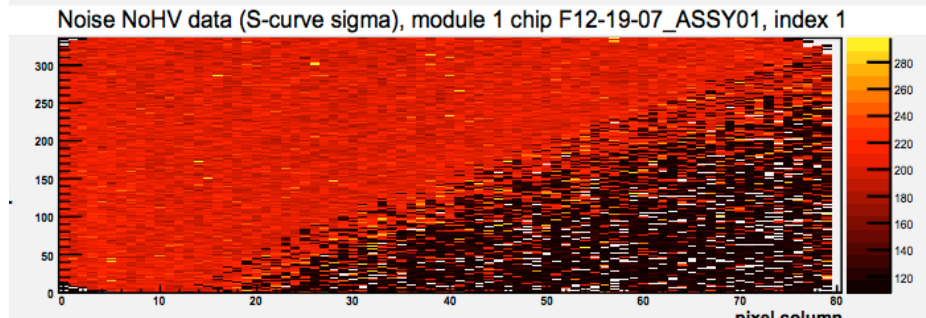
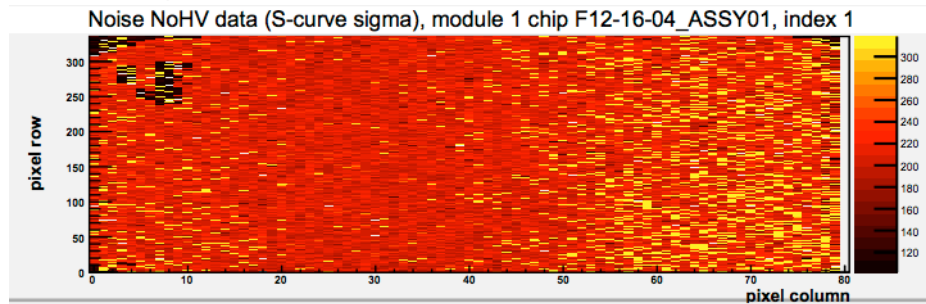
Pictures by I.Lopez



Table of FBK Rejected Bumps

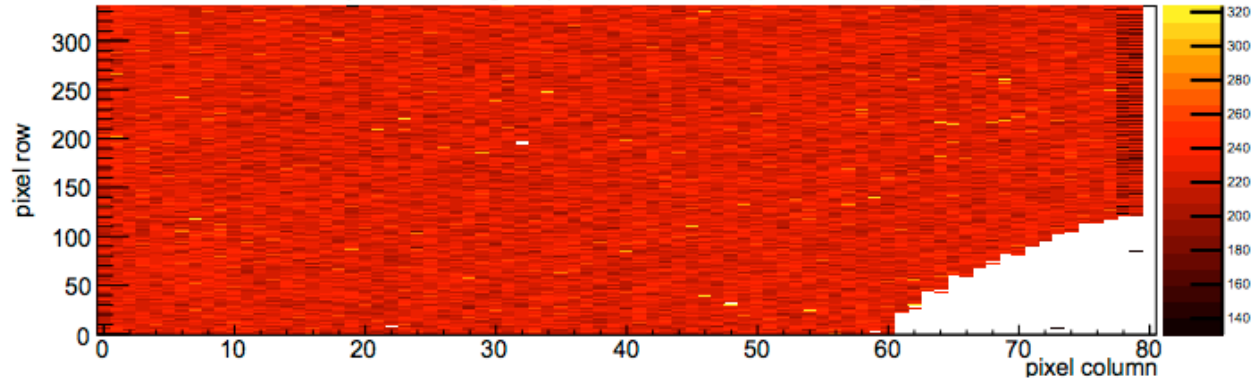
			F10-01-07	5	Göttingen
			F10-04-06	5	Göttingen
F10-18-02	1	Tamarack	F12-13-01	6	Tamarack
F10-18-06	1	Tamarack	F12-16-06	6	Tamarack
F10-22-08	1	Tamarack	F12-13-05	6	Tamarack
F10-07-01	2	Tamarack	F12-16-04	6	Tamarack
F10-07-03	2	Tamarack	F12-19-07	6	Tamarack
F10-18-08	2	Tamarack	F10-08-01	13	Göttingen
F12-02-02	2	Tamarack	F12-13-03	14	Göttingen
F12-02-08	2	Tamarack	F12-19-02	14	Göttingen
F12-19-05	2	Tamarack	F12-02-07	14	Göttingen
F10-08-03	2	Tamarack	F13-09-08	14	Göttingen
F12-13-01	2	Tamarack	F10-07-02	14	Göttingen
F10-20-07	2	Tamarack	F12-02-07	9	Tamarack
F10-04-03	3	Tamarack	F12-13-03	9	Tamarack
F10-18-07	3	Tamarack	F13-09-08	9	Tamarack
F12-07-05	3	Tamarack	F13-09-05	9	Tamarack
F10-02-06	3	Tamarack	F13-09-03	9	Tamarack
F12-07-08	3	Tamarack	F12-23-01	9	Tamarack
F12-19-02	3	Tamarack	F12-23-06	9	Tamarack
			F13-06-04	9	Tamarack
			F12-02-06	9	Tamarack

FBK Rejected Bumps (Batch 4,6)

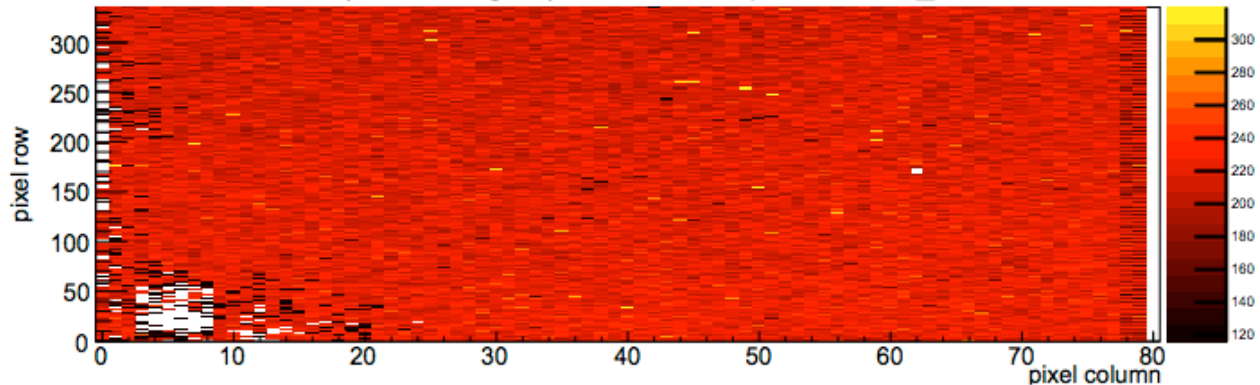


FBK Rejected Bumps (Batch 5,8,13)

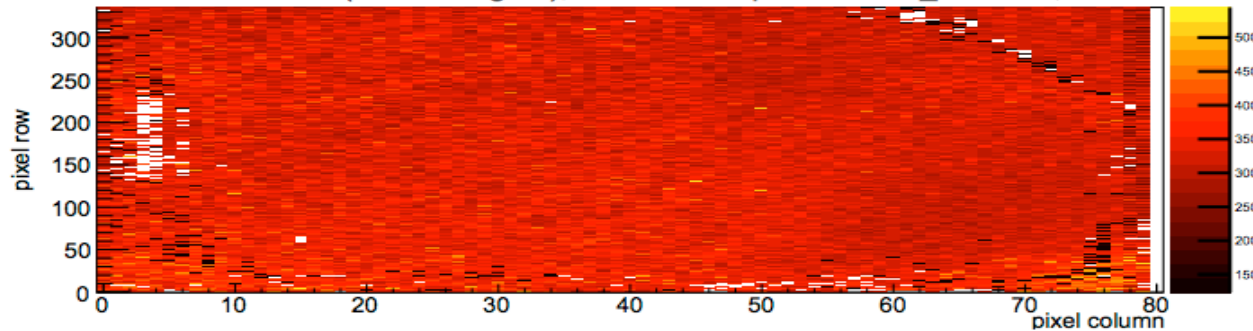
Noise NoHV data (S-curve sigma), module 1 chip F10-01-07_ASSY03, index 1



Noise NoHV data (S-curve sigma), module 1 chip F10-08-01_ASSY01, index 1



Noise NoHV data (S-curve sigma), module 1 chip F10-04-06_ASSY01, index 1



FBK Rejected Bumps (Batch 9)

